

# GTRA362802FC

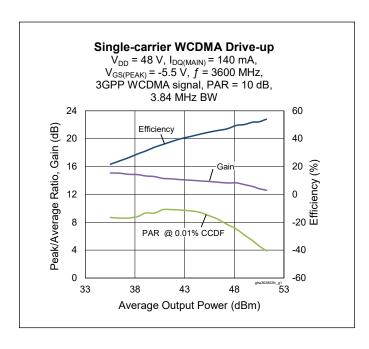
Thermally-Enhanced High Power RF GaN on SiC Amplifier, 280 W, 48 V, 3400 - 3600 MHz

#### **Description**

The GTRA362802FC is a 280-watt ( $P_{3dB}$ ) GaN on SiC HEMT D-mode amplifier designed for use in multi-standard cellular power amplifier applications. It features input matching, high efficiency, and a thermally-enhanced package with earless flange.



Package Types: H-37248C-4 PN: GTRA362802FC



#### **Features**

- GaN on SiC HEMT technology
- Input matched
- Asymmetrical Doherty design
  - Main: P<sub>3dB</sub> = 120 W Typ Peak: P<sub>3dB</sub> = 180 W Typ
- Typical Pulsed CW performance, 3400 3600 MHz, 48 V, combined outputs, 10 μs pulse width, 10% duty cycle
  - Output power at P<sub>3dB</sub> = 280 W
  - Drain Efficiency = 60%
  - Gain = 15 dB
- Capable of handling 10:1 VSWR @48 V, 44 W (CW) output power
- Human Body Model Class 1A (per ANSI/ESDA/ JEDEC JS-001)
- Low thermal resistance
- Pb-free and RoHS compliant

#### **RF Characteristics**

Single-carrier WCDMA Specifications (tested in the Doherty production test fixture)

 $\rm V_{DD}=48~V, I_{DQ}=140~mA, P_{OUT}=44~W~avg, V_{GS(PEAK)}=V_{GS}~@I_{DQ}=200~mA-2.2~V, f=3600~MHz, 3GPP~signal, channel~bandwidth=3.84~MHz, peak/average=10~dB~@~0.01\%~CCDF$ 

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Linear Gain	G <sub>ps</sub>	12	13.5	_	dB
Drain Efficiency	$\eta_{D}$	42.5	45.5	_	%
Adjacent Channel Power Ratio	ACPR	_	-29.5	-26.5	dBc
Output PAR @ 0.01% CCDF	OPAR	5.4	6.5	_	dB

All published data at T<sub>CASE</sub> = 25°C unless otherwise indicated ESD: Electrostatic discharge sensitive device—observe handling precautions!





#### **DC Characteristics**

Characteristic	Symbol	Min.	Тур.	Max.	Unit	Conditions
Drain-source Breakdown Voltage (main)	V	150			, ,	V - 0V   - 10 A
Drain-source Breakdown Voltage (peak)	V <sub>BR(DSS)</sub>	150	_	_	V	$V_{GS} = -8 \text{ V}, I_{D} = 10 \text{ mA}$
Drain-source Leakage Current	I <sub>DSS</sub>	_	_	7	mA	$V_{GS} = -8 \text{ V}, V_{DS} = 10 \text{ V}$
Gate Threshold Voltage (main)	V	-3.8	-3	-2.3	V	$V_{DS} = 10 \text{ V}, I_{D} = 14.4 \text{ mA}$
Gate Threshold Voltage (peak)	V <sub>GS(th)</sub>				V	$V_{DS} = 10 \text{ V}, I_{D} = 21.6 \text{ mA}$

#### **Recommended Operating Conditions**

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Drain Operating Voltage	V <sub>DD</sub>	0	_	50	, ,	
Gate Quiescent Voltage	V <sub>GS(Q)</sub>	-3.5	-3	-2.4	V	V <sub>DS</sub> =48 V, I <sub>D</sub> = 140 mA

## **Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit	
Drain-source Voltage	V <sub>DSS</sub>	125		
Gate-source Voltage	V <sub>GS</sub>	-10 to +2	V	
Operating Voltage	V <sub>DD</sub>	55		
Gate Current (main)		14.4	4	
Gate Current (peak)	I <sub>G</sub>	21.6	mA	
Drain Current (main)		5.4	Δ.	
Drain Current (peak)	I <sub>D</sub>	8.1	А	
Junction Temperature	T <sub>J</sub>	225		
Storage Temperature Range	T <sub>STG</sub>	-65 to +150	°C	

Operation above the maximum values listed here may cause permanent damage. Maximum ratings are absolute ratings; exceeding only one of these values may cause irreversible damage to the component. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. For reliable continuous operation, the device should be operated within the operating voltage range  $(V_{DD})$  specified above.

#### **Thermal Characteristics**

Characteristics	Symbol	Value	Unit	Conditions	
Thermal Resistance (main)	D	2.2	°C /\	T <sub>CASE</sub> = 70 °C, 67 W DC	
Thermal Resistance (peak)	$R_{ heta JC}$	1.5	°C/W	T <sub>CASE</sub> = 70 °C, 100 W DC	



#### **Ordering Information**

Type and Version Order Code		Package Description	Shipping	
GTRA362802FC V1 R0	GTRA362802FC-V1-R0	H-37248C-4, earless flange	Tape & Reel, 50 pcs	
GTRA362802FC V1 R2	GTRA362802FC-V1-R2	H-37248C-4, earless flange	Tape & Reel, 250 pcs	

#### **Typical Performance** (data taken in production test fixture)

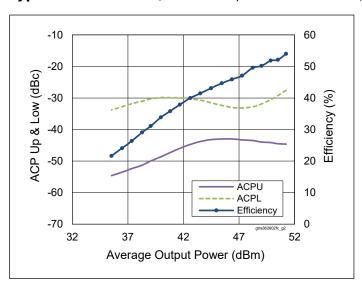


Figure 1. Single-carrier WCDMA Drive-up

 $V_{\rm DD} = 48~\rm V,~I_{\rm DQ(MAIN)} = 140~\rm mA, \\ V_{\rm GS(PEAK)} = -5.5~\rm V,~f = 3600~\rm MHz,~3GPP \\ \rm WCDMA~signal,~PAR = 10~\rm dB,~BW = 3.84~\rm MHz$ 

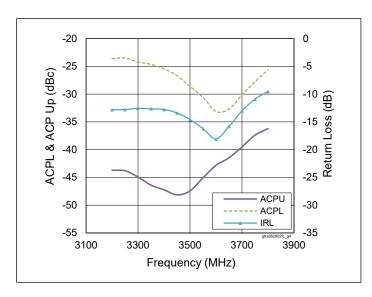


Figure 3. Single-carrier WCDMA Broadband Performance

$$\begin{split} &V_{DD}=48~V,~I_{DQ(MAIN)}=140~mA,\\ &V_{GS(PEAK)}=-5.5~V,~P_{OUT}=46.4~dBm,\\ &3GPP~WCDMA~signal,~PAR=10~dB \end{split}$$

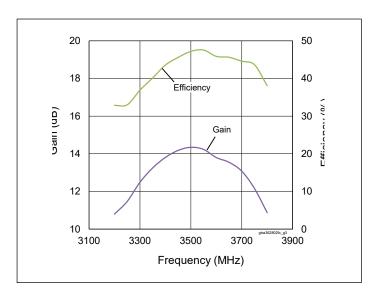


Figure 2. Single-carrier WCDMA Broadband Performance

$$\begin{split} &V_{DD}=48~V,~I_{DQ(MAIN)}=140~mA,\\ &V_{GS(PEAK)}=-5.5~V,~P_{OUT}=46.4~dBm,\\ &3GPP~WCDMA~signal,~PAR=10~dB \end{split}$$

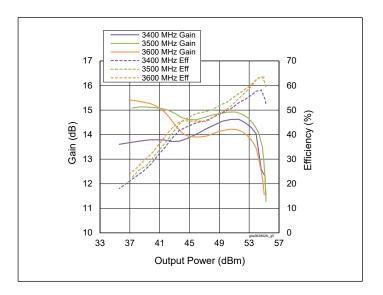
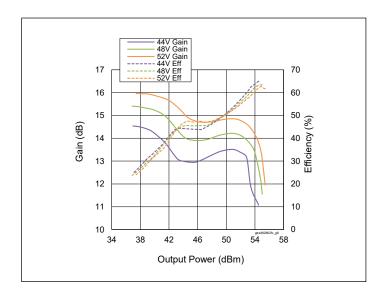


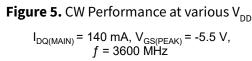
Figure 4. CW Performance

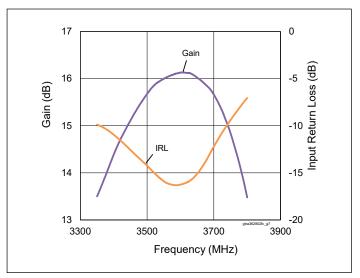
$$V_{DD}$$
 = 48 V,  $I_{DQ(MAIN)}$  = 140 mA,  $V_{GS(PEAK)}$  = -5.5 V



#### **Typical Performance (cont.)**







**Figure 6.** CW Performance Small Signal Gain & Input Return Loss

$$V_{DD}$$
 = 48 V,  $I_{DQ(MAIN)}$  = 140 mA,  $V_{GS(PEAK)}$  = -5.5 V

#### **Load Pull Performance**

**Main Side Load Pull Performance –** Pulsed CW signal: 10  $\mu$ s, 10% duty cycle, 48 V, I $_{DQ}$  = 200 mA, class AB

		$P_{3dB}$									
		Max Output Power						Max Dı	rain Efficie	ency	
Freq [MHz]	Zs [Ω]	Zl [Ω]	Gain [dB]	P <sub>3dB</sub> [dBm]	P <sub>3dB</sub> [W]	ηD [%]	Zl [Ω]	Gain [dB]	P <sub>3dB</sub> [dBm]	P <sub>3dB</sub> [W]	ηD [%]
3400	16-j19	5.9-j7.7	15	52.00	158.5	62.6	3.5-j4.8	16.6	50.10	102.3	74.0
3500	9.9-j11.5	9.4-j7.6	14.8	51.87	153.8	62.9	4.3-j5.2	16	50.52	112.7	71.5
3600	7.2-j6.5	7.1-j7.8	14.4	51.65	146.2	61.9	3.9-j4.7	15.9	49.70	93.3	71.6

Peak Side Load Pull Performance – Pulsed CW signal: 10  $\mu$ s, 10% duty cycle, 48 V,  $I_{DO}$  = 140 mA, class AB

			P <sub>3dB</sub>									
		Max Output Power					Max Output Power Max Drain Efficiency					
Freq [MHz]	Zs [Ω]	Zl [Ω]	Gain [dB]	P <sub>3dB</sub> [dBm]	P <sub>3dB</sub> [W]	ηD [%]	Zl [Ω]	Gain [dB]	P <sub>3dB</sub> [dBm]	P <sub>3dB</sub> [W]	ηD [%]	
3400	11.2-j9.2	3.9-j6.7	16	53.84	242.1	60.0	2.5-j4.8	17.8	52.30	170	71.0	
3500	7.6-j8.6	3.8-j7.2	16.1	53.73	236.1	58.7	2.7-j5.2	17.9	52.35	171.8	70.0	
3600	5.7-j9.5	4.6-j6.8	16.1	53.82	241	62.1	3.3-j4.8	17.1	52.60	182	68.6	

MACOM Technology Solutions Inc. (MACOM) and its affiliates reserve the right to make changes to the product(s) or information contained herein without notice.

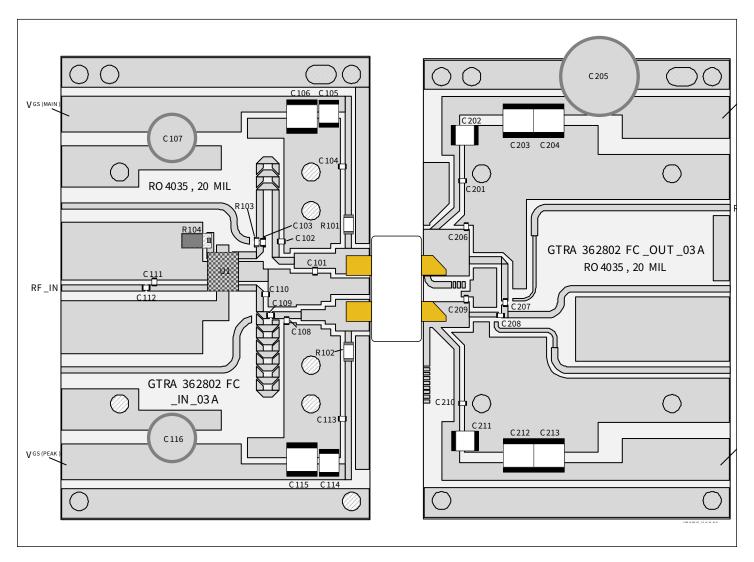
Visit <a href="https://www.macom.com">www.macom.com</a> for additional data sheets and product information.

For further information and support please visit:

Rev. 04.3, 2022-1-27



## Reference Circuit, 3400 - 3600 MHz



Reference circuit assembly diagram (not to scale)



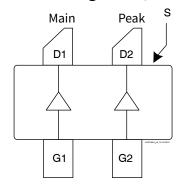
# **Reference Circuit Assembly**

DUT	GTRA362802FC-V1
Test Fixture Part No.	LTA/GTRA362802FC-V1
PCB	Rogers 4350, 0.508 mm [0.020"] thick, 2 oz. copper, $\varepsilon_r = 3.66$ , $f = 3400 - 3600$ MHz

# **Components Information**

Component	Description	Manufacturer	P/N
Input			
C101	Capacitor, 1.3 pF	ATC	ATC800A1R3CT250T
C102, C108	Capacitor, 0.5 pF	ATC	ATC800A0R5CT250T
C103, C104, C109, C112, C113	Capacitor, 12 pF	ATC	ATC800A120JT250T
C105, C114	Capacitor, 1 μF	TDK Corporation	C4532X7R2A105M230KA
C106, C115	Capacitor, 100 V, 10 μF	TDK Corporation	C5750X7S2A106M230KB
C107, C116	Capacitor, 100 μF	Panasonic Electronic Components	EEE-FP1V101AP
C110	Capacitor, 0.3 pF	ATC	ATC800A0R3CT250T
C111	Capacitor, 0.2 pF	ATC	ATC800A0R2CT250T
R101, R102	Resistor, 5.6 ohms	Panasonic Electronic Components	ERJ-8RQJ5R6V
R103	Resistor, 10 ohms	Panasonic Electronic Components	ERJ-3GEYJ100V
R104	Resistor, 50 ohms	Richardson	C16A50Z4
U1	Hybrid coupler	Anaren	XC3500P-03S
Output			
C201, C208, C210	Capacitor, 12 pF	ATC	ATC800A120JT250T
C202, C211	Capacitor, 1 μF	TDK Corporation	C4532X7R2A105M230KA
C203, C204, C212, C213	Capacitor, 100 V, 10 μF	TDK Corporation	C5750X7S2A106M230KB
C205	Capacitor, 220 μF	Panasonic Electronic Components	ECA-2AHG221
C206, C209	Capacitor, 0.4 pF	ATC	ATC800A0R4CT250T
C207	Capacitor, 15 pF	ATC	ATC800A150JT250T

# Pinout Diagram (top view)



# PinDescriptionD1Drain Device 1 (Main)D2Drain Device 2 (Peak)G1Gate Device 1 (Main)G2Gate Device 2 (Peak)SSource (flange)



# Package Outline Specifications - Package H-37248C-4

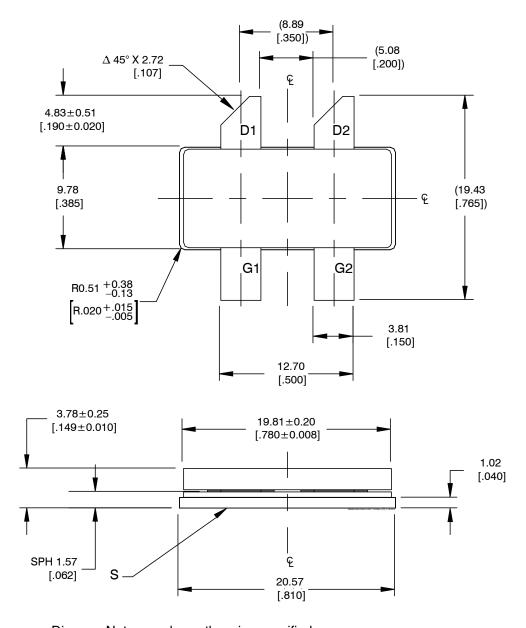


Diagram Notes—unless otherwise specified:

- 1. Interpret dimensions and tolerances per ASME Y14.5M-1994
- 2. Primary dimensions are mm, alternate dimensions are inches
- 3. All tolerances  $\pm 0.127$  [0.005]
- 4. Pins: D1, D2 drain, G1, G2 gate, S source (flange)
- 5. Lead thickness:  $0.13 \pm 0.05 [0.005 \pm 0.002]$
- 6. Gold plating thickness:  $1.14 \pm 0.38$  micron [45 ± 15 microinch]



#### Notes & Disclaimer

MACOM Technology Solutions Inc. ("MACOM"). All rights reserved.

These materials are provided in connection with MACOM's products as a service to its customers and may be used for informational purposes only. Except as provided in its Terms and Conditions of Sale or any separate agreement, MACOM assumes no liability or responsibility whatsoever, including for (i) errors or omissions in these materials; (ii) failure to update these materials; or (iii) conflicts or incompatibilities arising from future changes to specifications and product descriptions, which MACOM may make at any time, without notice. These materials grant no license, express or implied, to any intellectual property rights.

THESE MATERIALS ARE PROVIDED "AS IS" WITH NO WARRANTY OR LIABILITY, EXPRESS OR IMPLIED, RELATING TO SALE AND/OR USE OF MACOM PRODUCTS INCLUDING FITNESS FOR A PARTICULAR PURPOSE, MERCHANTABILITY, INFRINGEMENT OF INTELLECTUAL PROPERTY RIGHT, ACCURACY OR COMPLETENESS, OR SPECIAL, INDIRECT, INCIDENTAL, OR CONSEQUENTIAL DAMAGES WHICH MAY RESULT FROM USE OF THESE MATERIALS.

MACOM products are not intended for use in medical, lifesaving or life sustaining applications. MACOM customers using or selling MACOM products for use in such applications do so at their own risk and agree to fully indemnify MACOM for any damages resulting from such improper use or sale.